

Schottky Rectifier Diode

• Reverse voltage: 30 V

• Forward current: 2 A

• Low forward voltage: 0.53 V typ. @ 2 A

Low leakage current 40 μA typ. @ 30 V

• Low capacitance: 30 pF typ. @ 5 V

High ESD / transient robustness according to:

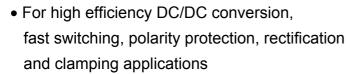
ESD (HBM): Class 3 B (> 8000 V)

ESD (MM): Class C (> 400 V)

ISO7637-2: Pulse 1 (-100 V, 2 ms)

Pulse 2 (-300 V, 50 μs)

Pulse 3 (-400 V, 100 ns)



- Very small SMD package (2.0 x 1.25 x 0.9 mm³) with improved operating temperature range due to extra-low thermal resistance design (see attached Forward current curves)
- Ideal to replace SMA packages with significant size advantage
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

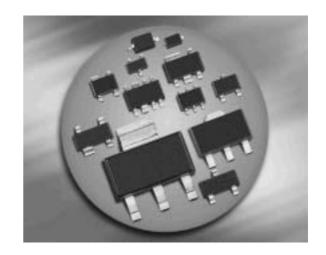




BAS3020B



| Туре | Package | Configuration | Marking |
|----------|---------|---------------|---------|
| BAS3020B | SOT363 | single | E9s |





Maximum Ratings at T_A = 25 °C, unless otherwise specified

| Parameter | Symbol | Value | Unit |
|---|---------------------|--------|------|
| Diode reverse voltage ¹⁾ | V_{R} | 30 | V |
| Peak reverse voltage ¹⁾ | V_{RM} | 30 | |
| RMS reverse voltage ¹⁾ | V _{R(RMS)} | 21 | |
| Forward current ¹⁾²⁾ , $T_S \le 96^{\circ}C$ | I _F | 2 | Α |
| Repetitive peak forward current ²⁾ | / _{FRM} | 3.5 | |
| $(t_p \le 1 \text{ ms}, D \le 0.5)$ | | | |
| Non-repetitive peak surge forward current ²⁾ | I _{FSM} | 10 | |
| (<i>t</i> ≤ 10ms) | | | |
| Junction temperature | T_{j} | 150 | °C |
| Operating temperature range | Top | -55125 | |
| Storage temperature | T _{stg} | -65150 | |

Thermal Resistance

| Parameter | Symbol | Value | Unit |
|--|-------------------|-------|------|
| Junction - soldering point ³⁾ | R _{thJS} | ≤ 42 | K/W |

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-------------------------------|----------------|--------|------|------|------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Reverse current ⁴⁾ | I _R | | | | μΑ |
| $V_{R} = 5 \text{ V}$ | | _ | 5 | 25 | |
| V _R = 10 V | | _ | 10 | 50 | |
| V _R = 30 V | | - | 40 | 200 | |
| Forward voltage ⁴⁾ | V _F | | | | mV |
| $I_{\rm F}$ = 500 mA | | _ | 350 | 410 | |
| / _F = 1 A | | - | 410 | 470 | |
| I _F = 2 A | | _ | 530 | 600 | |

 $^{^{1}}$ For T_{A} > 25 $^{\circ}$ C the derating of VR and IF has to be considered. Please refer to the attached curves.

²Only valid if pins 3 and 4 are connected in parallel.

 $^{^3\}mbox{For calculation of}\,R_{\mbox{\scriptsize thJA}}$ please refer to Application Note Thermal Resistance.

⁴Pulsed test: $t_{\rm p} \le 300~\mu{\rm s};~D = \le 0.02$



30

20

40

30



 $V_{R} = 5 \text{ V}, f = 1 \text{ MHz}$

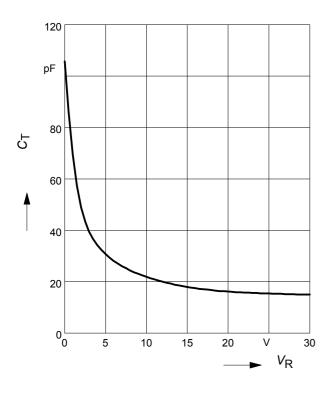
 V_{R} = 10 V, f = 1 MHz

| Parameter | Symbol | Values | | | Unit |
|-------------------------------------|----------------|--------|------|------|------|
| | | min. | typ. | max. | |
| AC Characteristics | | | | | |
| Diode capacitance | C _T | | | | pF |
| $V_{\rm P} = 1 \rm V, f = 1 MHz$ | | _ | 60 | 70 | |



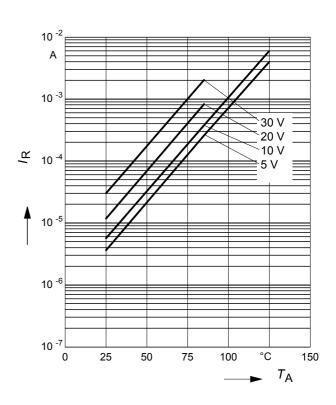
Diode capacitance $C_T = f(V_R)$

f = 1MHz



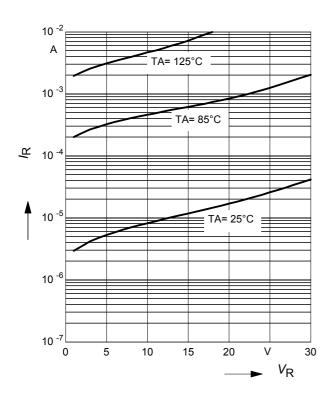
Reverse current $I_R = f(T_A)$

 V_{R} = Parameter



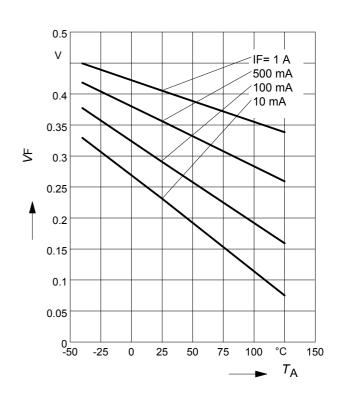
Reverse current $I_R = f(V_R)$

 T_A = Parameter



Forward Voltage $V_F = f(T_A)$

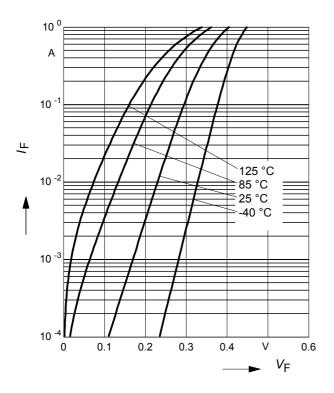
 I_{F} = Parameter





Forward current $I_F = f(V_F)$

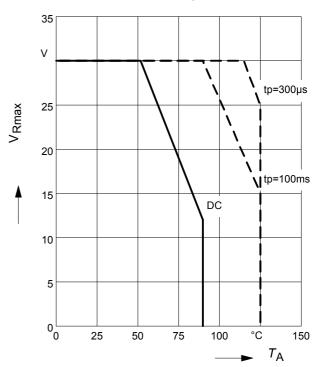
 T_A = Parameter



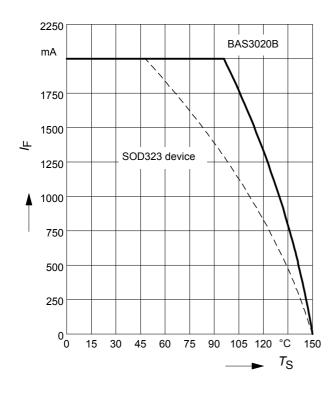
Permissible Reverse voltage $V_R = f(T_A)$

 t_p = Parameter, Duty cycle < 0.01

Device mounted on PCB with R_{th} = 160 k/W

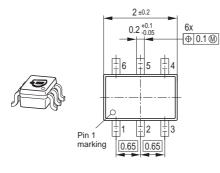


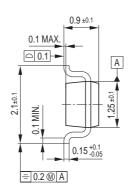
Forward current $I_F = f(T_S)$



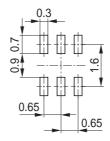


Package Outline



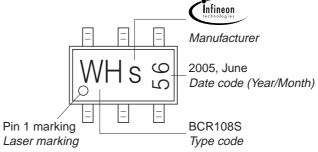


Foot Print



Marking Layout (Example)

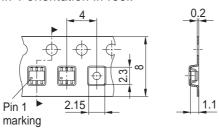
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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